

TSM60N750CP ROG

TSM60N750CP ROG Information

Heisener.com

Part Number TSM60N750CP ROG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET, SINGLE, N-CHANNEL, SUPER**Package**TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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TSM60N750CP ROG Specifications

Manufacturer Part Number TSM60N750CP ROG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 10.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 554pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs10.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds554pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)62.5W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs10.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds554pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)62.5W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature Supplier Device Package Package / Case 6A (Tc) 6	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs10.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds554pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)62.5W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 10.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 554pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	6A (Tc)
Gate Charge (Qg) (Max) @ Vgs 10.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 554pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 554pF @ 100V Vgs (Max) #30V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	10.8nC @ 10V
FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	554pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs750 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	62.5W (Tc)
Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	750 mOhm @ 3A, 10V
Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252, (D-Pak)
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

TSM60N750CP ROG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM60N750CP ROG Payment Methods



















TSM60N750CP ROG Shipping Methods













If you have any question about TSM60N750CP ROG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com